LMC6442 Dual Micropower Rail-to-Rail Output Single Supply Operational Amplifier

Check for Samples: LMC6442

FEATURES

- **(Typical, V_S = 2.2V)**
- **Output Swing to Within 30 mV of Supply Rail**
- **High Voltage Gain 103 dB**
- **Gain Bandwidth Product 9.5 KHz**
- **Ensured for: 2.2V, 5V, 10V**
- **Low Supply Current 0.95 µA/Amplifier**
- **Input Voltage Range −0.3V to V^+ -0.9V**
- **2.1 µW/Amplifier Power Consumption**
- **Stable for $A_V \geq +2$ or $A_V \leq -1$**

APPLICATIONS

- **Portable Instruments**
- **Smoke/Gas/CO/Fire Detectors**
- **Pagers/Cell Phones**
- **Instrumentation**
- **Thermostats**
- **Occupancy Sensors**
- **Cameras**
- **Active Badges**

DESCRIPTION

The LMC6442 is ideal for battery powered systems, where very low supply current (less than one microamp per amplifier) and Rail-to-Rail output swing is required. It is characterized for 2.2V to 10V operation, and at 2.2V supply, the LMC6442 is ideal for single (Li-Ion) or two cell (NiCad or alkaline) battery systems.

The LMC6442 is designed for battery powered systems that require long service life through low supply current, such as smoke and gas detectors, and pager or personal communications systems.

Operation from single supply is enhanced by the wide common mode input voltage range which includes the ground (or negative supply) for ground sensing applications. Very low (5 fA, typical) input bias current and near constant supply current over supply voltage enhance the LMC6442's performance near the end-of-life battery voltage.

Designed for closed loop gains of greater than plus two (or minus one), the amplifier has typically 9.5 KHz GBWP (Gain Bandwidth Product). Unity gain can be used with a simple compensation circuit, which also allows capacitive loads of up to 300 pF to be driven, as described in the Application Information section.

Connection Diagram

Top View

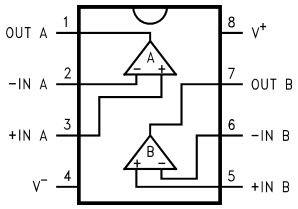

Figure 1. 8-Pin SOIC / PDIP Package
See Package Numbers D0008A, P0008E

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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Absolute Maximum Ratings (1)(2)

ESD Tolerance (3)	2 kV
Differential Input Voltage	±Supply Voltages
Voltage at Input/Output Pin	(V^+) + 0.3V, (V^-) − 0.3V
Supply Voltage $(V^+ - V^-)$:	16V
Current at Input Pin (4)	±5 mA
Current at Output Pin (5) (6)	±30 mA
Lead Temp. (soldering 10 sec)	260°C
Storage Temp. Range:	−65°C to +150°C
Junction Temp. (7)	150°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
(2) If Military/Aerospace specified devices are required, please contact the TI Sales Office/ Distributors for availability and specifications.
(3) Human body model, 1.5 kΩ in series with 100 pF.
(4) Limiting input pin current is only necessary for input voltages that exceed absolute maximum input voltage ratings.
(5) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.
(6) Do not short circuit output to V^+, when V^+ is greater than 13V or reliability will be adversely affected.
(7) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.

Operating Ratings (1)

Supply Voltage		$1.8V \le V_S \le 11V$
Junction Temperature Range: LMC6442AI, LMC6442I		$-40°C < T_J < +85°C$
Thermal Resistance (θ_{JA})	D0008A Package, 8-pin Surface Mount	193°C/W
	P0008E Package, 8-pin Molded DIP	115°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.

2.2V Electrical Characteristics

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 2.2V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
DC Electrical Characteristics						
V_{OS}	Input Offset Voltage		−0.75	±3 **±4**	±7 **±8**	mV max
TCV_{OS}	Temp. coefficient of input offset voltage		0.4			µV/°C
I_B	Input Bias Current	See (3)	0.005	**4**	**4**	pA max
I_{OS}	Input Offset Current	See (3)	0.0025	**2**	**2**	pA max
CMRR	Common Mode Rejection Ratio	$-0.1V \le V_{CM} \le 0.5V$	92	67 **67**	67 **67**	dB min
C_{IN}	Common Mode Input Capacitance		4.7			pF
PSRR	Power Supply Rejection Ratio	V_S = 2.5 V to 10V	95	75 **75**	75 **75**	dB min

(1) Typical Values represent the most likely parametric norm.
(2) All limits are specified by testing or statistical analysis unless otherwise specified.
(3) Limits specified by design.

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2.2V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 2.2V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
V_{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	1.3	1.05 **0.95**	1.05 **0.95**	V min
			−0.3	−0.2 **0**	−0.2 **0**	V max
A_V	Large Signal Voltage Gain	Sourcing (4)	100			dB min
		Sinking (4)	94			
		V_O = 0.22V to 2V	103	80	80	
V_O	Output Swing	V_{ID} = 100 mV (5)	2.18	2.15 **2.15**	2.15 **2.15**	V min
		V_{ID} = −100 mV (5)	22	60 **60**	60 **60**	mV max
I_{SC}	Output Short Circuit Current	Sourcing, V_{ID} = 100 mV (6) (5)	50	18 **17**	18 **17**	µA min
		Sinking, V_{ID} = −100 mV (6) (5)	50	20 **19**	20 **19**	
I_S	Supply Current (2 amplifiers)	R_L = open	1.90	2.4 **3.0**	2.6 **3.2**	µA max
		V^+ = 1.8V, R_L = open	2.10			
AC Electrical Characteristics						
SR	Slew Rate (7)		2.2			V/ms
GBWP	Gain-Bandwidth Product		9.5			KHz
φ_m	Phase Margin	See (8)	63			deg

(4) R_L connected to $V^+/2$. For Sourcing Test, $V_O > V^+/2$. For Sinking tests, $V_O < V^+/2$.
(5) V_{ID} is differential input voltage referenced to inverting input.
(6) Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test.
(7) Slew rate is the slower of the rising and falling slew rates.
(8) See the Typical Performance Characteristics and Applications Information sections for more details.

5V Electrical Characteristics

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
DC Electrical Characteristics						
V_{OS}	Input Offset Voltage		−0.75	±3 **±4**	±7 **±8**	mV max
TCV_{OS}	Temp. coefficient of input offset voltage		0.4			µV/°C
I_B	Input Bias Current	See (3)	0.005	**4**	**4**	pA max
I_{OS}	Input Offset Current	See (3)	0.0025	**2**	**2**	pA max
CMRR	Common Mode Rejection Ratio	−0.1V ≤ V_{CM} ≤3.5V	102	70 **70**	70 **70**	dB min
C_{IN}	Common Mode Input Capacitance		4.1			pF
PSRR	Power Supply Rejection Ratio	V_S = 2.5 V to 10V	95	75 **75**	75 **75**	dB min

(1) Typical Values represent the most likely parametric norm.
(2) All limits are specified by testing or statistical analysis unless otherwise specified.
(3) Limits specified by design.

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5V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 5V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
V_{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	4.1	3.85 **3.75**	3.85 **3.75**	V min
			−0.4	−0.2 **0**	−0.2 **0**	V max
A_V	Large Signal Voltage Gain	Sourcing (4)	100			dB min
		Sinking (4)	94			
		V_O = 0.5V to 4.5V	103	80	80	
V_O	Output Swing	V_{ID} = 100 mV (5)	4.99	4.95 **4.95**	4.95 **4.95**	V min
		V_{ID} = −100 mV (5)	20	50 **50**	50 **50**	mV max
I_{SC}	Output Short Circuit Current	Sourcing, V_{ID} = 100 mV (6) (5)	500	300 **200**	300 **200**	µA min
		Sinking, V_{ID} = −100 mV (6) (5)	350	200 **150**	200 **150**	
I_S	Supply Current (2 amplifiers)	R_L = open	1.90	2.4 **3.0**	2.6 **3.2**	µA max
AC Electrical Characteristics						
SR	Slew Rate (7)		4.1	2.5	2.5	V/ms
GBWP	Gain-Bandwidth Product		10			KHz
φ_m	Phase Margin	See (8)	64			deg
THD	Total Harmonic Distortion	A_V = +2, f = 100 Hz, R_L = 10 MΩ, V_{OUT} = 1 V_{PP}	0.08			%

(4) R_L connected to $V^+/2$. For Sourcing Test, $V_O > V^+/2$. For Sinking tests, $V_O < V^+/2$.
(5) V_{ID} is differential input voltage referenced to inverting input.
(6) Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test.
(7) Slew rate is the slower of the rising and falling slew rates.
(8) See the Typical Performance Characteristics and Applications Information sections for more details.

10V Electrical Characteristics

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 10V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
DC Electrical Characteristics						
V_{OS}	Input Offset Voltage		−1.5	±3 **±4**	±7 **±8**	mV max
TCV_{OS}	Temp. coefficient of input offset voltage		0.4			µV/°C
I_B	Input Bias Current	See (3)	0.005	**4**	**4**	pA max
I_{OS}	Input Offset Current	See (3)	0.0025	**2**	**2**	pA max
CMRR	Common Mode Rejection Ratio	−0.1V ≤ V_{CM} ≤8.5V	105	70 **70**	70 **70**	dB min
C_{IN}	Common Mode Input Capacitance		3.5			pF
PSRR	Power Supply Rejection Ratio	V_S= 2.5 V to 10V	95	75 **75**	75 **75**	dB min

(1) Typical Values represent the most likely parametric norm.
(2) All limits are specified by testing or statistical analysis unless otherwise specified.
(3) Limits specified by design.

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10V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for T_J = 25°C, V^+ = 10V, V^- = 0V, $V_{CM} = V_O = V^+/2$, and R_L = 1 MΩ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Typ (1)	LMC6442AI Limit (2)	LMC6442I Limit (2)	Units
V_{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	9.1	8.85 **8.75**	8.85 **8.75**	V min
			−0.4	−0.2 **0**	−0.2 **0**	V max
A_V	Large Signal Voltage Gain	Sourcing (4)	120			dB min
		Sinking (4)	100			
		V_O = 0.5V to 9.5V	104	80	80	
V_O	Output Swing	V_{ID} = 100 mV (5)	9.99	9.97 **9.97**	9.97 **9.97**	V min
		V_{ID} = −100 mV (5)	22	50 **50**	50 **50**	mV max
I_{SC}	Output Short Circuit Current	Sourcing, V_{ID} = 100 mV (6) (5)	2100	1200 **1000**	1200 **1000**	µA min
		Sinking, V_{ID} = −100 mV (6) (5)	900	600 **500**	600 **500**	
I_S	Supply Current (2 amplifiers)	R_L = open	1.90	2.4 **3.0**	2.6 **3.2**	µA max
AC Electrical Characteristics						
SR	Slew Rate (7)		4.1	2.5	2.5	V/ms
GBWP	Gain-Bandwidth Product		10.5			KHz
φ_m	Phase Margin	See (8)	68			deg
e_n	Input-Referred Voltage Noise	R_L = open f = 10 Hz	170			nV/√Hz
i_n	Input-Referred Current Noise	R_L = open f = 10 Hz	0.0002			pA/√Hz
	Crosstalk Rejection	See (9)	85			dB

(4) R_L connected to $V^+/2$. For Sourcing Test, $V_O > V^+/2$. For Sinking tests, $V_O < V^+/2$.
(5) V_{ID} is differential input voltage referenced to inverting input.
(6) Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test.
(7) Slew rate is the slower of the rising and falling slew rates.
(8) See the Typical Performance Characteristics and Applications Information sections for more details.
(9) Input referred, V^+ = 10V and R_L = 10 MΩ connected to 5V. Each amp excited in turn with 1 KHz to produce about 10 V_{PP} output.

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Typical Performance Characteristics

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Total Supply Current vs. Supply Voltage

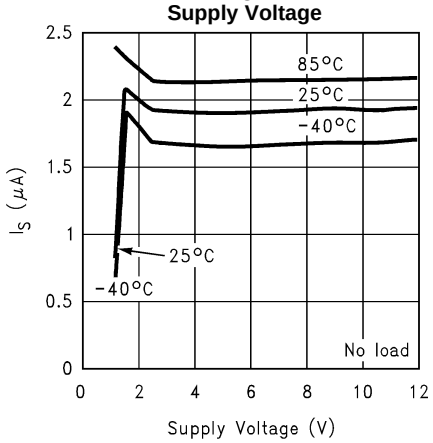

Figure 2.

Total Supply Current vs. Supply Voltage (Negative Input Overdrive)

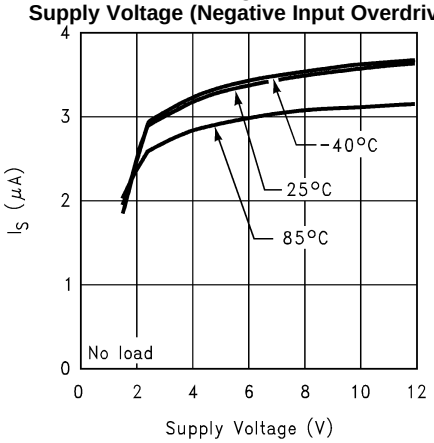

Figure 3.

Total Supply Current vs. Supply Voltage (Positive Input Overdrive)

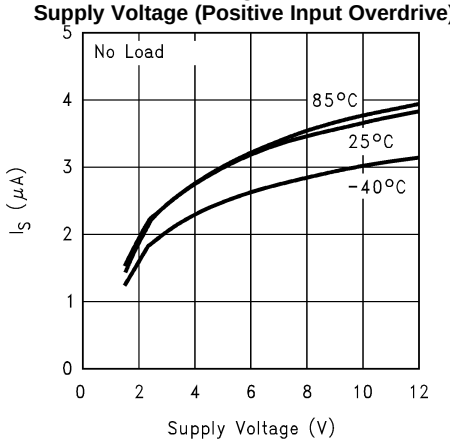

Figure 4.

Input Bias Current vs. Temperature

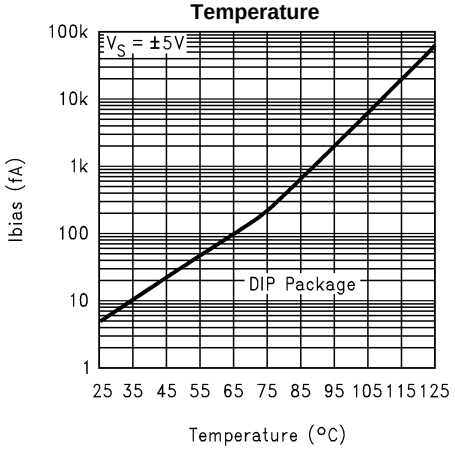

Figure .

Offset Voltage vs. Common Mode Voltage (V_S = 2.2V)

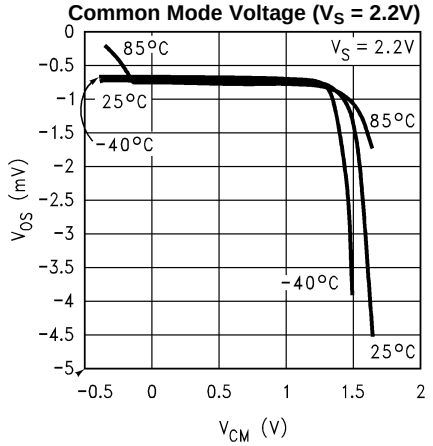

Figure 5.

Offset Voltage vs. Common Mode Voltage (V_S = 5V)

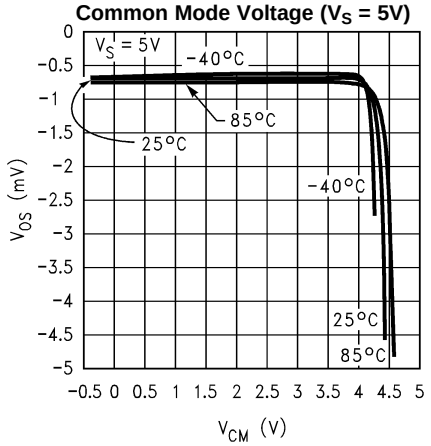

Figure 6.

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Typical Performance Characteristics (continued)

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Offset Voltage vs. Common Mode Voltage (V_S = 10V)

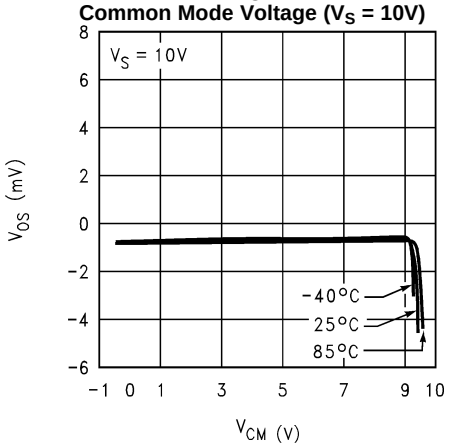

Figure 7.

Swing Towards V⁻ vs. Supply Voltage

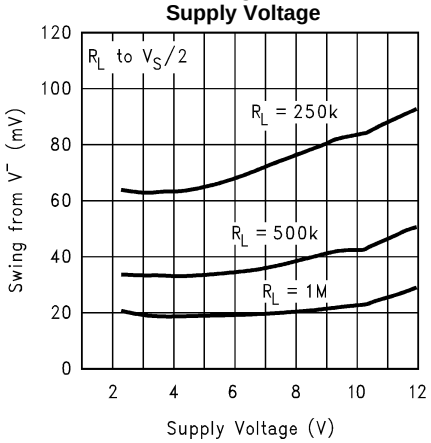

Figure 8.

Swing Towards V⁺ vs. Supply Voltage

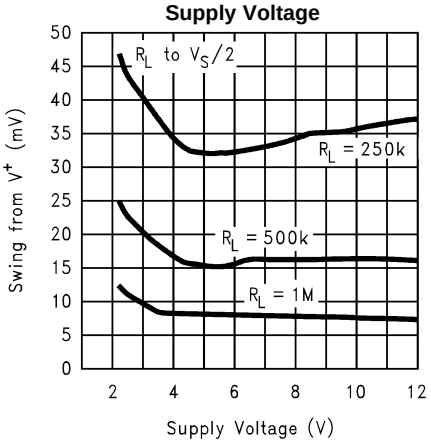

Figure 9.

Swing From Rail(s) vs. Temperature

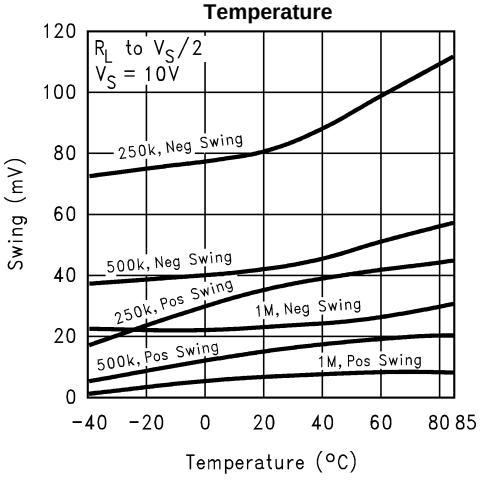

Figure 10.

Output Source Current vs. Output Voltage

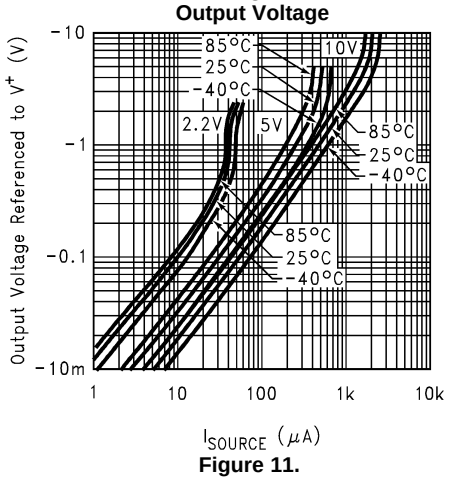

Figure 11.

Output Sink Current vs. Output Voltage

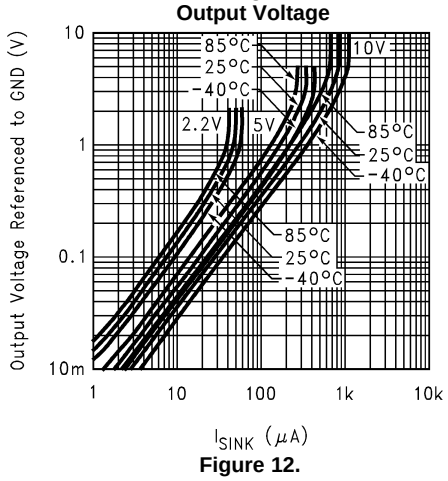

Figure 12.

Typical Performance Characteristics (continued)

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Maximum Output Voltage vs. Load Resistance

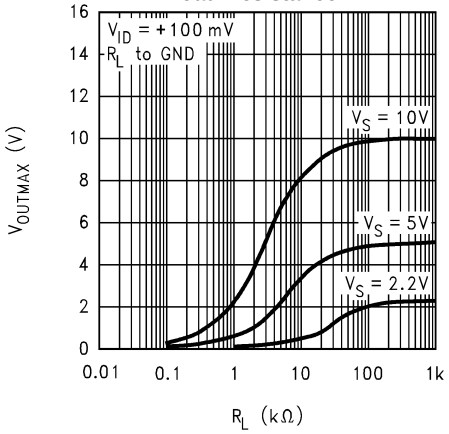

Figure 13.

Large Signal Voltage Gain vs. Supply Voltage

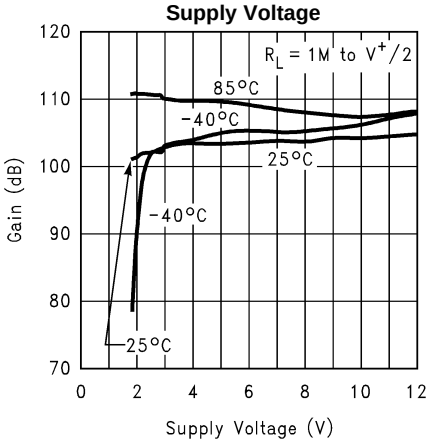

Figure 14.

Open Loop Gain/Phase vs. Frequency

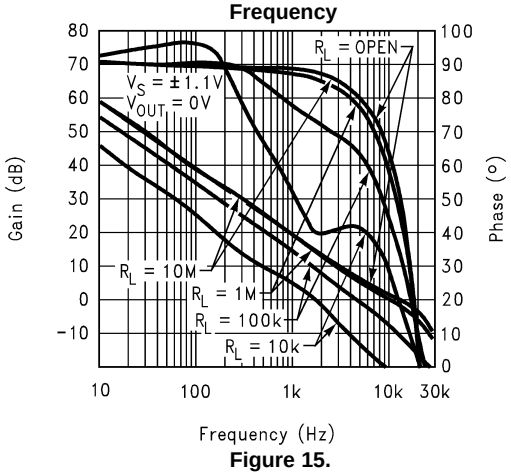

Figure 15.

Open Loop Gain/Phase vs. Frequency For Various C_L (Z_L = 1 MΩ II C_L)

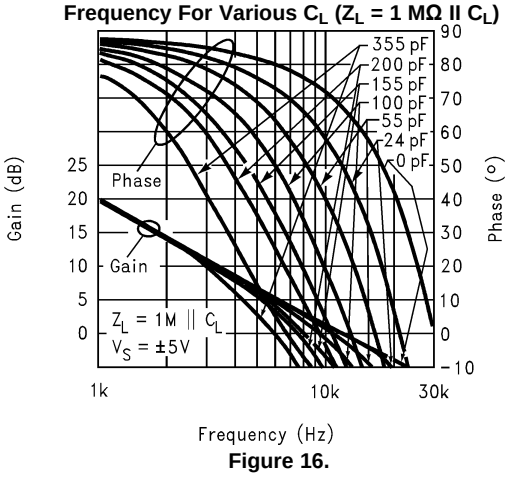

Figure 16.

Open Loop Gain/Phase vs. Frequency For Various C_L (Z_L = 100 KΩ II C_L)

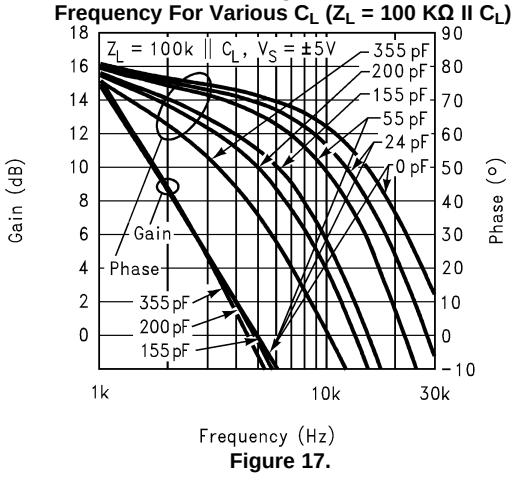

Figure 17.

Gain Bandwidth Product vs. Supply Voltage

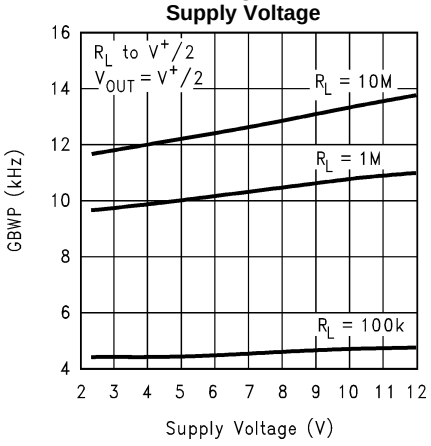

Figure 18.

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Typical Performance Characteristics (continued)

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Phase Margin (Worst Case) vs. Supply Voltage

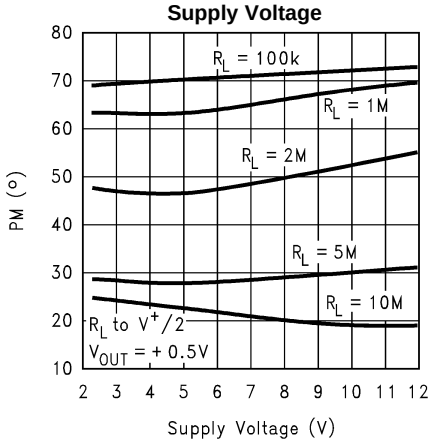

Figure 19.

CMRR vs. Frequency

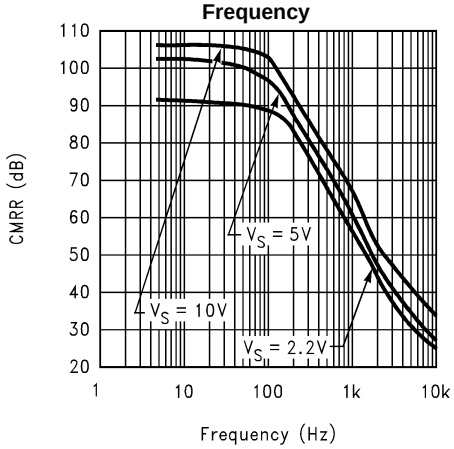

Figure 20.

PSRR vs. Frequency

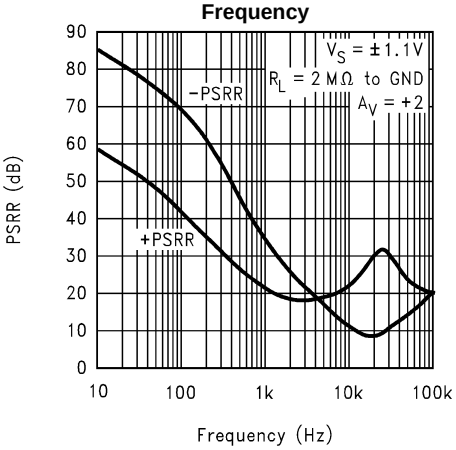

Figure 21.

Positive Slew Rate vs. Supply Voltage

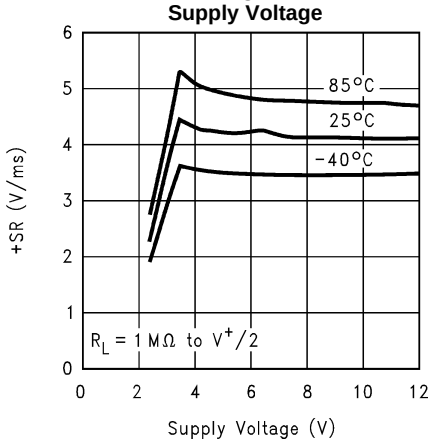

Figure 22.

Negative Slew Rate vs. Supply Voltage

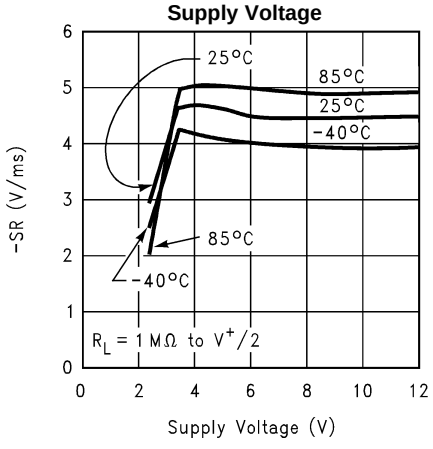

Figure 23.

Cross-Talk Rejection vs. Frequency

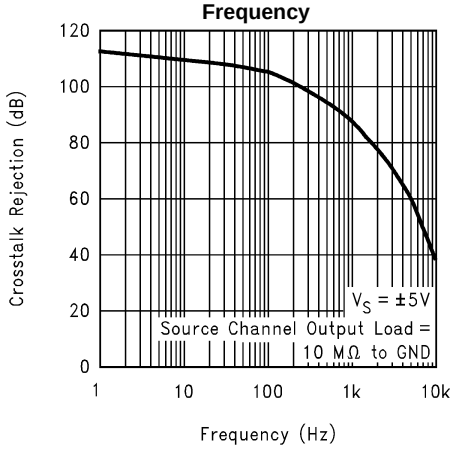

Figure 24.

Typical Performance Characteristics (continued)

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Input Voltage Noise vs. Frequency

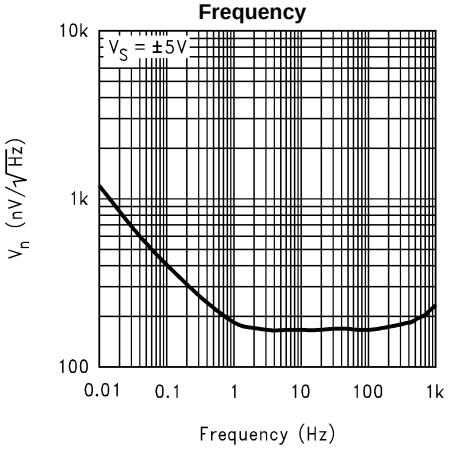

Figure 25.

Output Impedance vs. Frequency

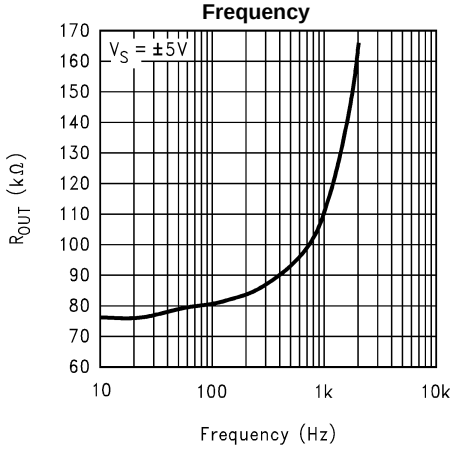

Figure 26.

THD+N vs. Frequency

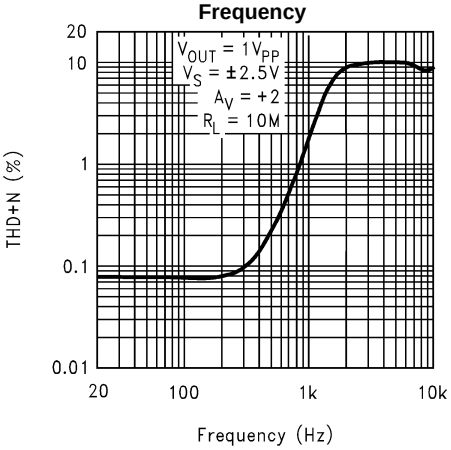

Figure 27.

THD+N vs. Amplitude

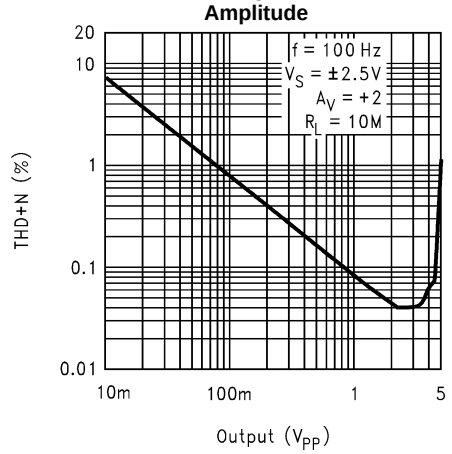

Figure 28.

Maximum Output Swing vs. Frequency

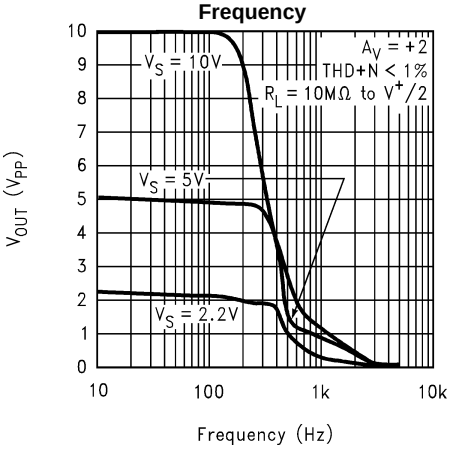

Figure 29.

Small Signal Step Response (A_V = +2) (C_L = 12 pF, 100 pF)

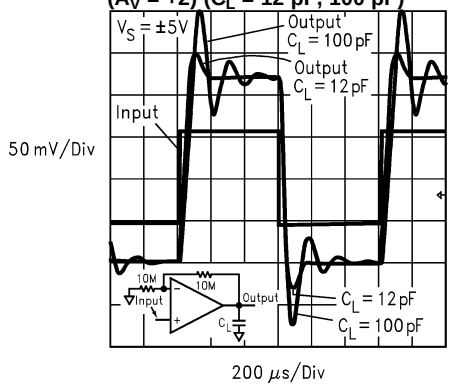

Figure 30.

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Typical Performance Characteristics (continued)

V_S = 5V, Single Supply, T_A = 25°C unless otherwise specified

Large Signal Step Response
(A_V = +2) (C_L = 100 pF)

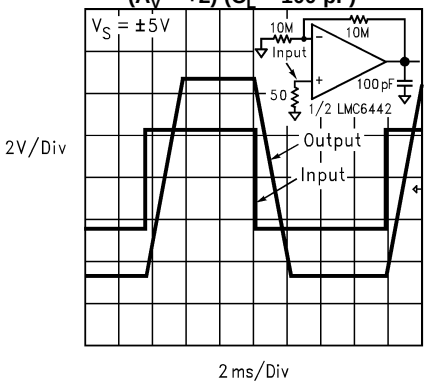

Figure 31.

Small Signal Step Response
(A_V = −1) (C_L = 1MΩ II 100 pF, 200 pF)

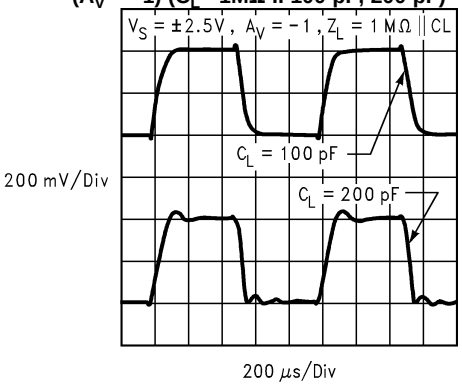

Figure 32.

Small Signal Step Response
(A_V = +1) For Various C_L

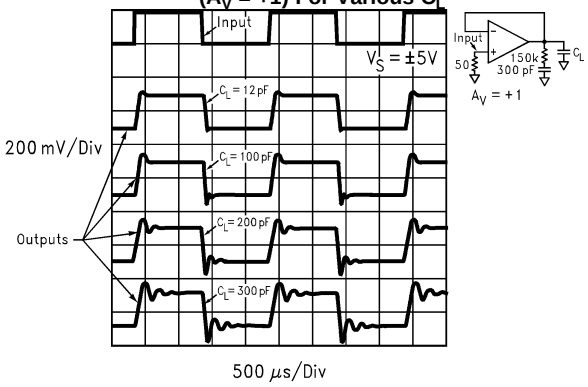

Figure 33.

Large Signal Step Response
(A_V = +1) (C_L = 200 pF)

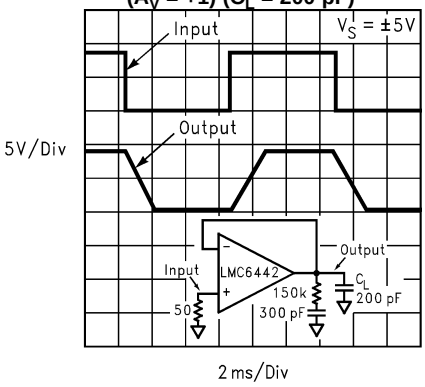

Figure 34.

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APPLICATIONS INFORMATION

USING LMC6442 IN UNITY GAIN APPLICATIONS

LMC6442 is optimized for maximum bandwidth and minimal external components when operating at a minimum closed loop gain of +2 (or −1). However, it is also possible to operate the device in a unity gain configuration by adding external compensation as shown in Figure 35:

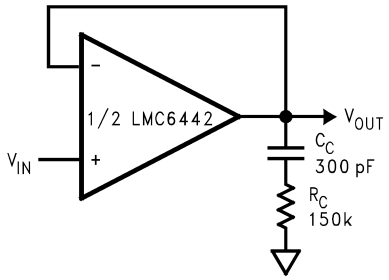

Figure 35. A_V = +1 Operation by adding C_C and R_C

Using this compensation technique it is possible to drive capacitive loads of up to 300 pF without causing oscillations (see the Typical Performance Characteristics for step response plots). This compensation can also be used with other gain settings in order to improve stability, especially when driving capacitive loads (for optimum performance, R_C and C_C may need to be adjusted).

USING "T" NETWORK

Compromises need to be made whenever high gain inverting stages need to achieve a high input impedance as well. This is especially important in low current applications which tend to deal with high resistance values. Using a traditional inverting amplifier, gain is inversely proportional to the resistor value tied between the inverting terminal and input while the input impedance is equal to this value. For example, in order to build an inverting amplifier with an input impedance of 10MΩ and a gain of 100, one needs to come up with a feedback resistor of 1000 MΩ -an expensive task.

An alternate solution is to use a "T" Network in the feedback path, as shown in Figure 36.

Closed loop gain, A_V is given by:

$$A_V = -\frac{R^2}{R2} \bullet \left(\frac{2}{R} + \frac{1}{R1}\right) \quad (1)$$

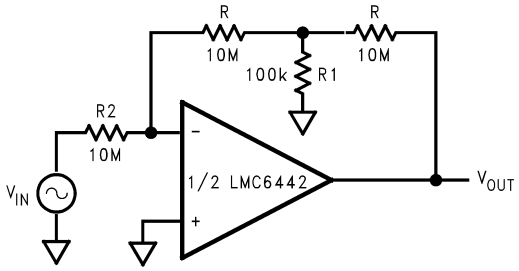

Figure 36. "T" Network Used to Replace High Value Resistor

It must be noted, however, that using this scheme, the realizable bandwidth would be less than the theoretical maximum. With feedback factor, β, defined as:

$$\beta \cong \frac{R2}{R2 + R} \bullet \frac{R1}{R1 + R} \quad \text{for } R2 \gg R1 \quad (2)$$

$$BW(-3\ dB) \approx GBWP \bullet \beta \quad (3)$$

In this case, assuming a GBWP of about 10 KHz, the expected BW would be around 50 Hz (vs. 100 Hz with the conventional inverting amplifier).

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Looking at the problem from a different view, with R_F defined by A_V•Rin, one could select a value for R in the "T" Network and then determine R1 based on this selection:

$$R1 = \frac{R^2}{R_F - 2R} \tag{4}$$

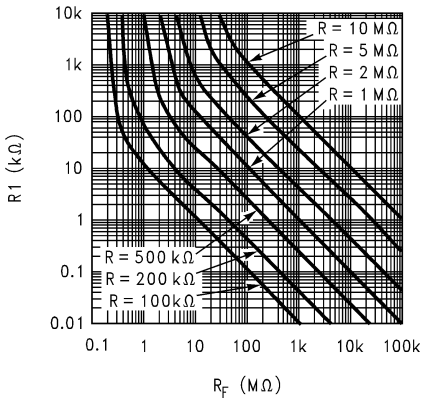

Figure 37. "T" Network Values for Various Values of R

For convenience, Figure 37 shows R1 vs. R_F for different values of R.

DESIGN CONSIDERATIONS FOR CAPACITIVE LOADS

As with many other opamps, the LMC6442 is more stable at higher closed loop gains when driving a capacitive load. Figure 38 shows minimum closed loop gain versus load capacitance, to achieve less than 10% overshoot in the output small signal response. In addition, the LMC6442 is more stable when it provides more output current to the load and when its output voltage does not swing close to V^-.

The LMC6442 is more tolerant to capacitive loads when the equivalent output load resistance is lowered or when output voltage is 1V or greater from the V^- supply. The capacitive load drive capability is also improved by adding an isolating resistor in series with the load and the output of the device. Figure 39 shows the value of this resistor for various capacitive loads (A_V = −1), while limiting the output to less than 10 % overshoot.

Referring to the Typical Performance Characteristics plot of Phase Margin (Worst Case) vs. Supply Voltage, note that Phase Margin increases as the equivalent output load resistance is lowered. This plot shows the expected Phase Margin when the device output is very close to V^-, which is the least stable condition of operation. Comparing this Phase Margin value to the one read off the Open Loop Gain/Phase vs. Frequency plot, one can predict the improvement in Phase Margin if the output does not swing close to V^-. This dependence of Phase Margin on output voltage is minimized as long as the output load, R_L, is about 1MΩ or less.

Output Phase Reversal: The LMC6442 is immune against this behavior even when the input voltages exceed the common mode voltage range.

Output Time Delay: Due to the ultra low power consumption of the device, there could be as long as 2.5 ms of time delay from when power is applied to when the device output reaches its final value.

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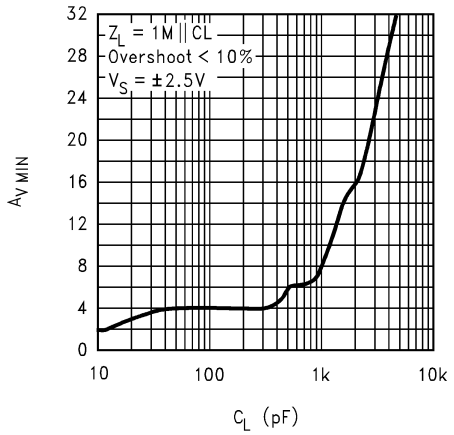

Figure 38. Minimum Operating Gain vs. Capacitive Load

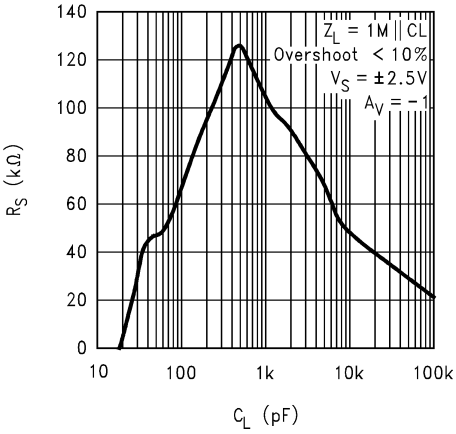

Figure 39. Isolating Resistor Value vs Capacitive Load

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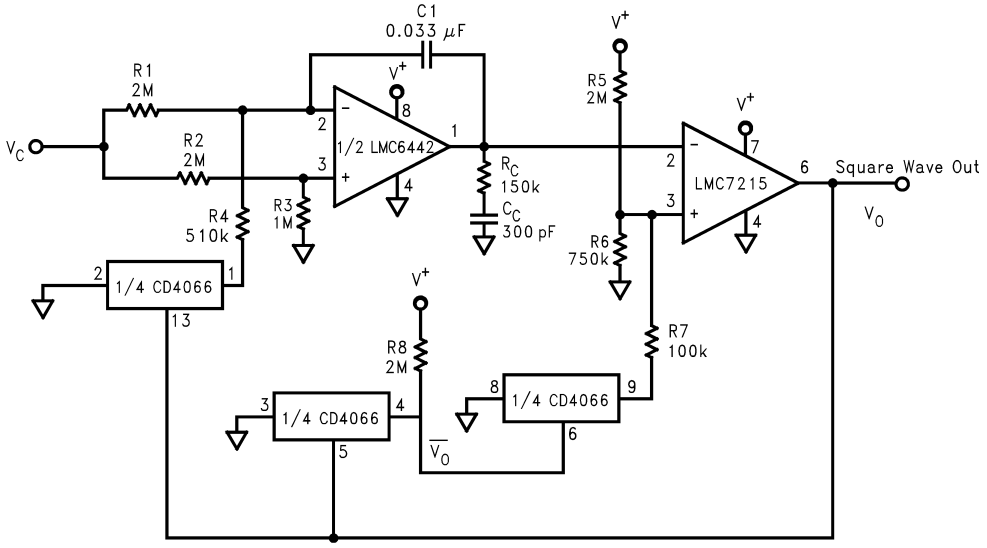
Application Circuits



V^+ = 5V: I_S < 10 µA, f/V_C = 4.3 (Hz/V)

$$R1 \cong 4R4$$

$$R2 = 2R3$$

$$f(Hz) = \frac{V_C}{3R_1C_1V^+\left[\frac{R6}{R5+R6} - \frac{(R6 \,||\, R7)}{(R6 \,||\, R7)+R5}\right]} \cong \frac{V_C(R5+R6)}{3R_1C_1V^+(R6-R7)} \quad \text{for } R5 >> R6 \text{ and } R6 >> R7$$

Figure 40. Micropower Single Supply Voltage to Frequency Converter

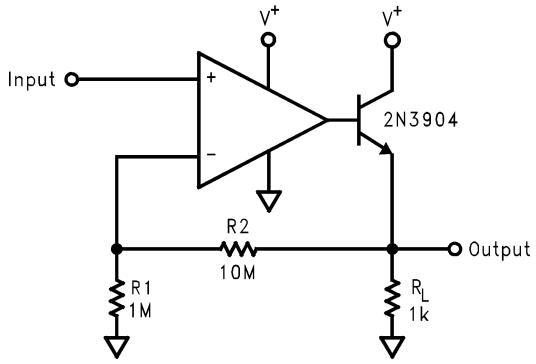


Figure 41. Gain Stage with Current Boosting

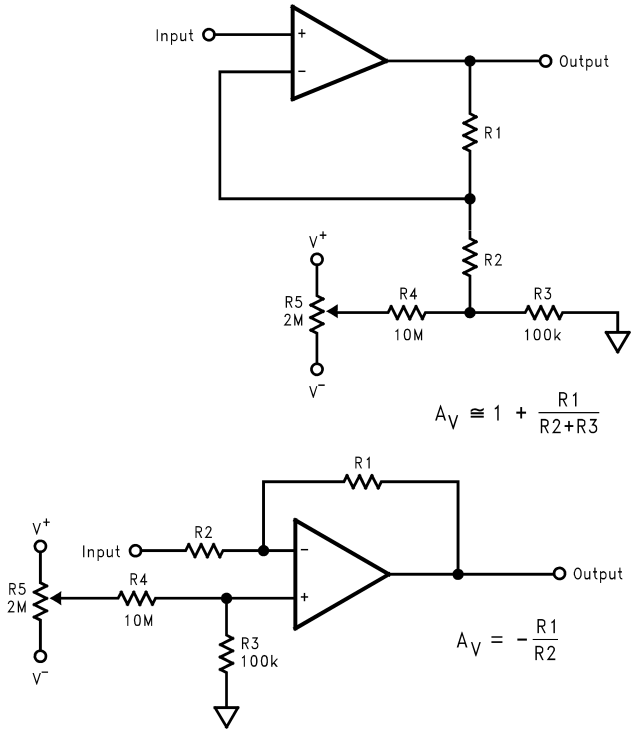


Figure 42. Offset Nulling Schemes

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REVISION HISTORY

Changes from Revision D (March 2013) to Revision E	Page
• Changed layout of National Data Sheet to TI format	16

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMC6442AIM/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42AIM	Samples
LMC6442AIMX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42AIM	Samples
LMC6442IM/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42IM	Samples
LMC6442IMX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI | SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42IM	Samples
LMC6442IN/NOPB	ACTIVE	PDIP	P	8	40	RoHS & Green	Call TI	Level-1-NA-UNLIM	-40 to 85	LMC6442 IN	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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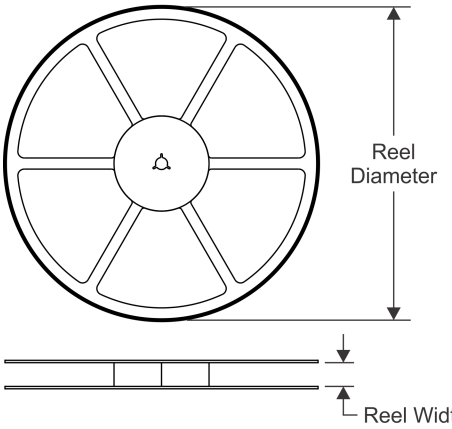
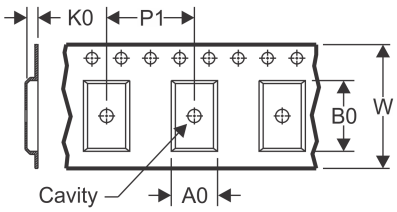
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

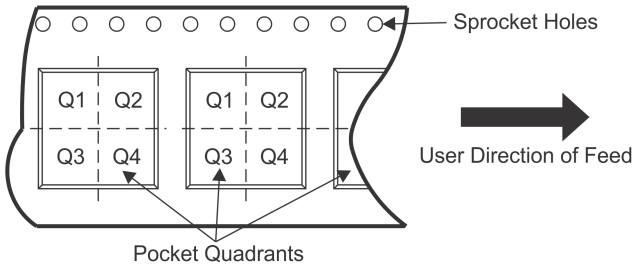


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

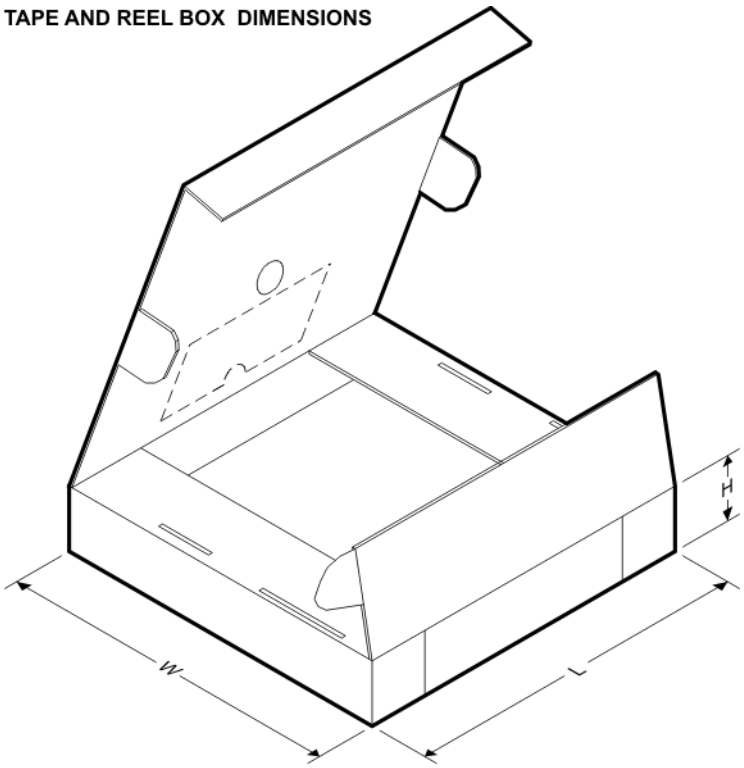
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMC6442AIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMC6442IMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

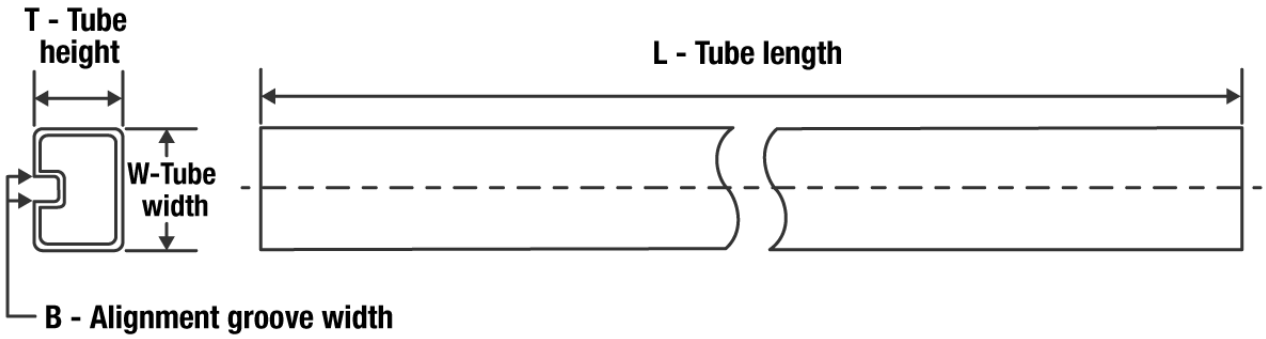
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

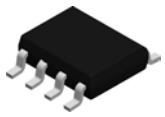
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMC6442AIMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMC6442IMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LMC6442AIM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LMC6442IM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LMC6442IN/NOPB	P	PDIP	8	40	502	14	11938	4.32

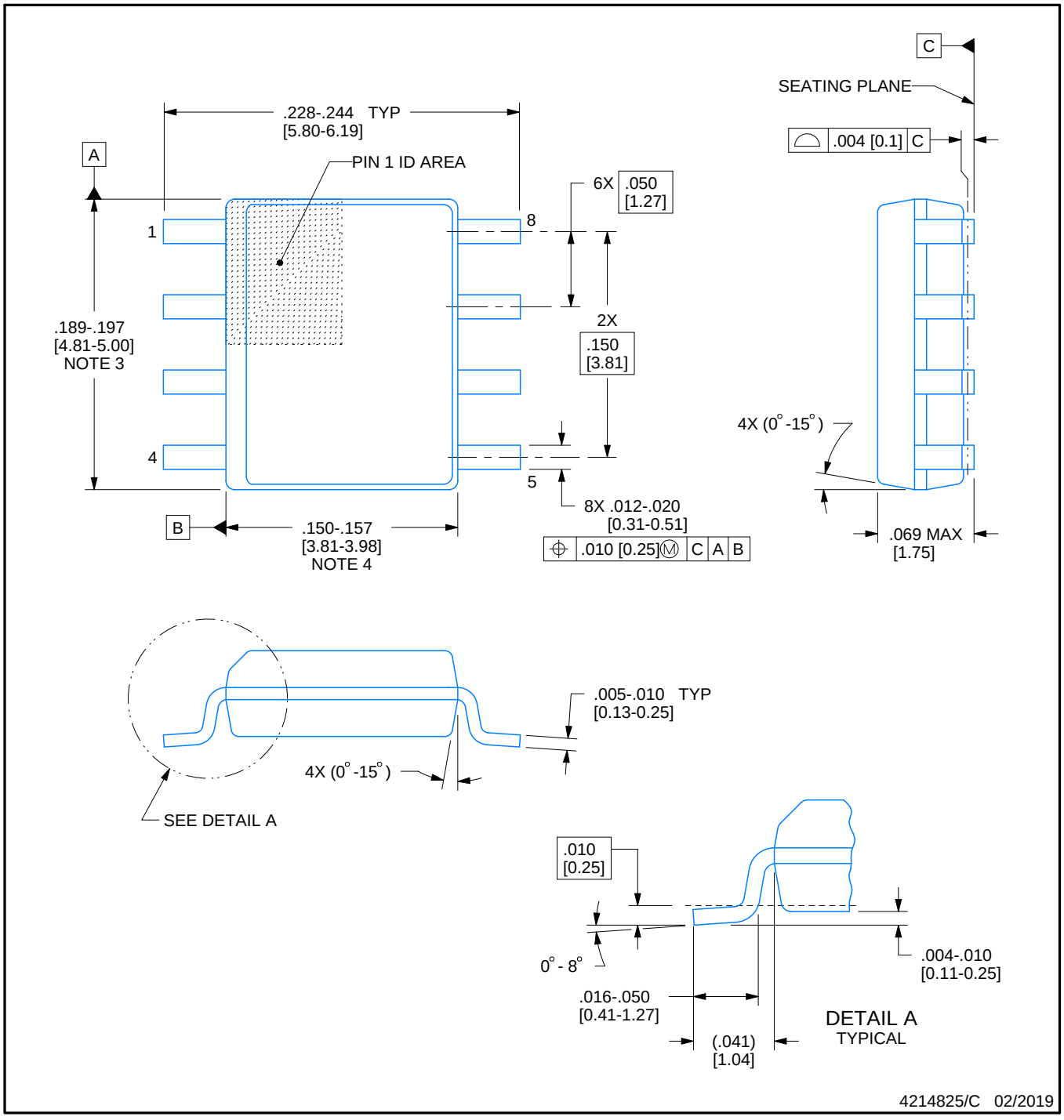


PACKAGE OUTLINE

D0008A

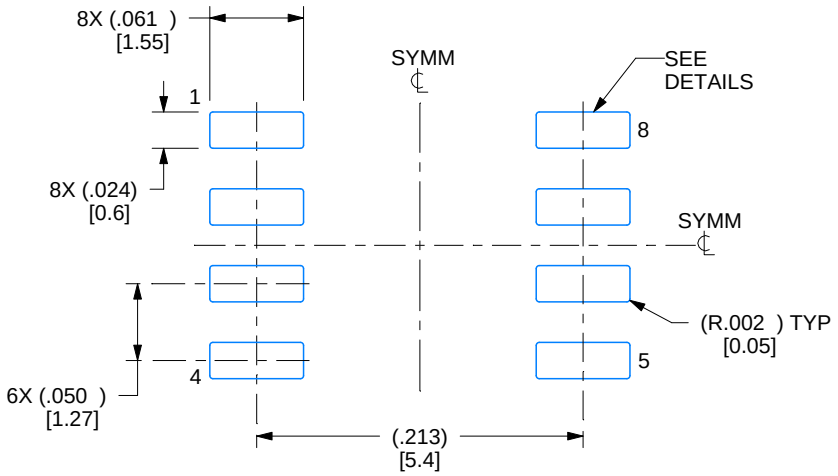
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

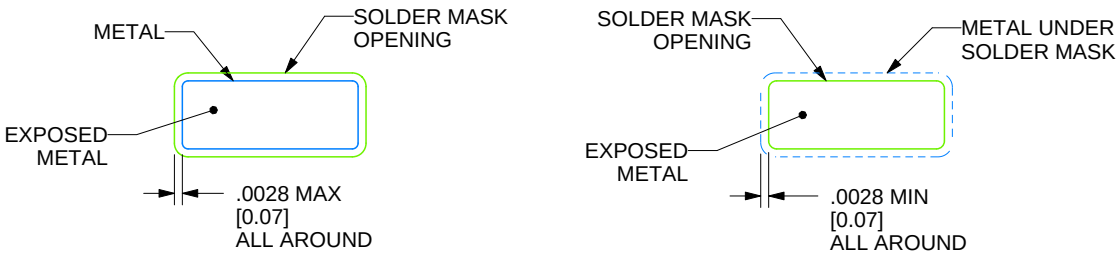


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

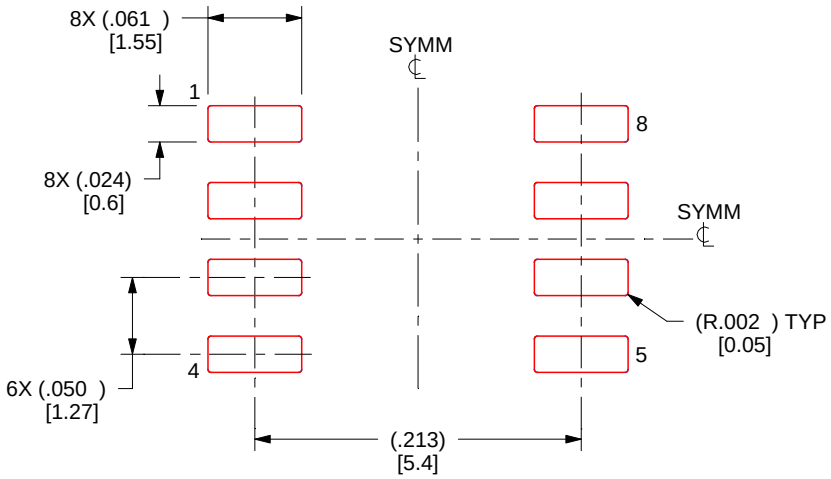
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



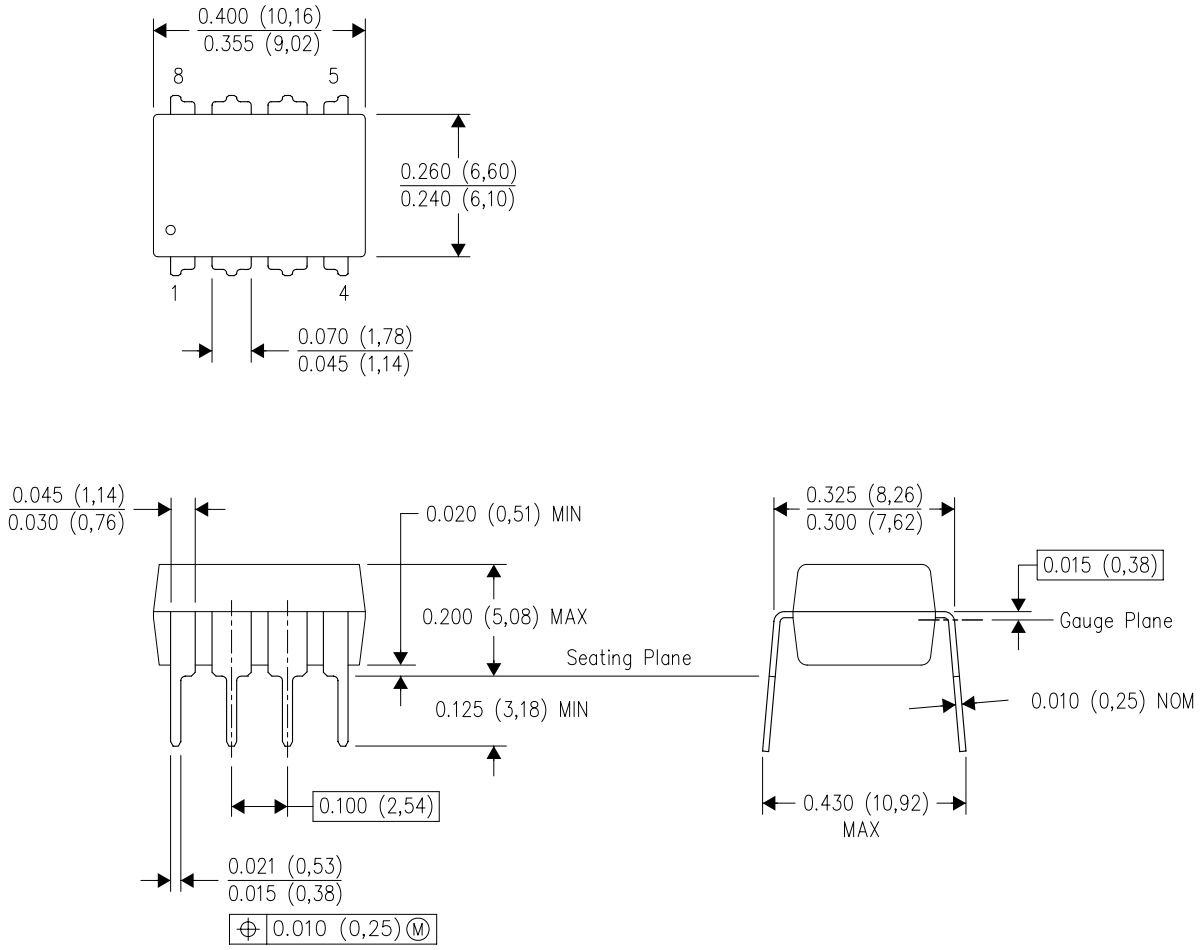
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R–PDIP–T8) PLASTIC DUAL–IN–LINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001 variation BA.

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